



2025 MPW schedule

Last updated: February 26, 2025

| MPW name | Fab | Processes | Tape-In | Ship Date |
|---------------------------------|---------------|--|--------------------|-----------|
| PH18DA - B5614 | NPB - Fab 3 | SiPho 0.18um | 8-20-24 | 8-7-25 |
| PH18M* - B5617 | NPB - Fab 3 | SiPho 0.18um | 9-10-24 | 5-5-25 |
| SB*18 - B5619 | NPB - Fab 3 | SiGe BiCMOS 0.18um | 10-08-24 | 4-28-25 |
| CS18* - B5616 | MH - Fab 2 | CMOS-SOI 0.18um | 10-29-24 | |
| CA18 - B5621 | NPB - Fab 3 | RFCMOS 0.18um | 11-05-24 | 4-29-25 |
| SB*18 - B5622 | NPB - Fab 3 | SiGe BiCMOS 0.18um | 11-19-24 | 6-20-25 |
| SB*18 - B6000 | NPB - Fab 3 | SiGe BiCMOS 0.18um | 1-14-25 | 8-27-25 |
| Q1 2025 | NM - Fab 11 | TPS65MSPM | 2-04-25 | |
| CA18 - B6002 | NPB - Fab 3 | RFCMOS 0.18um | 2-11-25 | 8-21-25 |
| 32nd MPW - Tonami, Japan | TPSCo - Fab 5 | CMOS 0.18u & 0.16u, PM, PM_SOI | 2-25-25 | |
| PH18M* - B6003 | NPB - Fab 3 | SiPho 0.18um | 2-25-25 | 10-20-25 |
| 1 st MPW RFSOI-RSM5T | TSIT - Fab 10 | 90RSC/65RSA2/65RSB2/65RSC | 3-10-25 | |
| 34th MPW - Uozu, Japan | TPSCo - Fab 7 | CMOS, PM, RFCMOS & SiGe, 65nm : TPS65SLA/SLC, TPS65PMA/PMB/PMK/MSA/MSB/MSK, TPS65RF, TPS65SG | 3-24-25 | |
| PH18DA - B6006 | NPB - Fab 3 | SiPho 0.18um | 3-25-25 | 3-12-26 |
| SB*18 - B6007 | TJT - Fab 9 | SiGe BiCMOS 0.18um | 4-08-25 | |
| SH125T18APRIL | MH - Fab 2 | CIS 0.18u Image Sensor CMOS+ 0.16u, 0.18u RF, RFID, PM | 4-10-25 4-17-25 | |
| 35th MPW - Uozu, Japan | TPSCo - Fab 7 | 300mm Silicon Photonics: TPS45PHD | 4-14-25 | |
| SBC18HE5PCA - B6008 | NPB - Fab 3 | SiGe BiCMOS 0.18um with PCM RF Switch | 4-22-25 | |
| CA18 - B6009 | NPB - Fab 3 | RFCMOS 0.18um | 5-06-25 | 11-13-25 |
| Q2 2025 | NM - Fab 11 | TPS65MSPM | 5-15-25 | |
| PH18M* - B6010 | NPB - Fab 3 | SiPho 0.18um | 5-20-25 | 1-12-26 |
| 33rd MPW - Tonami, Japan | TPSCo - Fab 5 | CMOS 0.18u & 0.16u, PM, PM_SOI | 5-26-25 | |
| SB*18 - B6011 | NPB - Fab 3 | SiGe BiCMOS 0.18um | 6-03-25 | 12-22-25 |
| CS18* - B6012 | MH - Fab 2 | CMOS-SOI 0.18um | 6-17-25 | |
| SB*/CA13* - B6013 | NPB - Fab 3 | SiGe BiCMOS/RF CMOS 0.13um | 7-01-25 | 3-3-26 |
| SBC18HE5PCA - B6014 | NPB - Fab 3 | SiGe BiCMOS 0.18um with PCM RF Switch | 7-15-25 | |
| SB*18 - B6015 | NPB - Fab 3 | SiGe BiCMOS 0.18um | 7-29-25 | 2-16-26 |
| PH18DA - B6016 | NPB - Fab 3 | SiPho 0.18um | 8-12-25 | 7-30-26 |

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| Q3 2025 | NM - Fab 11 | TPS65MSPM | 8-15-25 | |
| 34th MPW - Tonami, Japan | TPSCo - Fab 5 | CMOS 0.18u & 0.16u, PM, PM_SOI | 8-25-25 | |
| CA18 - B6017 | NPB - Fab 3 | RFCMOS 0.18um | 8-26-25 | 2-06-26 |
| 2nd MPW RFSOI-RSS5T | TSIT - Fab 10 | 90RSC/65RSA2/65RSB2/65RSC | 9-8-25 | |
| PH18M* - B6019 | NPB - Fab 3 | SiPho 0.18um | 9-23-25 | 5-18-26 |
| 36th MPW - Uozu, Japan | TPSCo - Fab 7 | CMOS, PM, RFCMOS & SiGe, 65nm : TPS65SLA/SLC, TPS65PMA/PMB/PMK/MSA/MSB/MSK, TPS65RF, TPS65SG | 9-29-25 | |
| SB*18 - B6020 | NPB - Fab 3 | SiGe BiCMOS 0.18um | 10-07-25 | 4-16-26 |
| SBC18HE5PCA - B6021 | NPB - Fab 3 | SiGe BiCMOS 0.18um with PCM RF Switch | 10-21-25 | |
| 37th MPW - Uozu, Japan | TPSCo - Fab 7 | 300mm Silicon Photonics: TPS45PHD | 10-27-25 | |
| PH18M* - B6022 | NPB - Fab 3 | SiPho 0.18um | 10-28-25 | 6-22-26 |
| Q4 2025 | NM - Fab 11 | TPS65MSPM | 11-14-25 | |
| SH225T18NOV | MH - Fab 2 | CIS 0.18u Image Sensor CMOS+ 0.16u, 0.18u RF, RFID, PM | 11-17-25 11-23-25 | |
| 35th MPW - Tonami, Japan | TPSCo - Fab 5 | CMOS 0.18u & 0.16u, PM, PM_SOI | 11-25-25 | |
| CS18* - B6023 | MH - Fab 2 | CMOS-SOI 0.18um | 1-6-26 | |

Notes: "Shuttles" (SH*) are run at Fab 2

* 0.13u MH – fab 2 Shuttle / MPW slots will be considered per needs

Please contact your customer account manager for additional information.

Fab2 - Tower Semiconductor 200mm wafer fabrication facility at Migdal Ha'emek, Israel

Fab3 - Tower Semiconductor 200mm wafer fabrication facility at Newport Beach, CA

Fab5 - Tower Semiconductor 200mm wafer fabrication facility at Tonami, Japan

Fab7 - Tower Semiconductor 300mm wafer fabrication facility at Uozu, Japan

Fab9 - Tower Semiconductor 200mm wafer fabrication facility at San Antonio, TX

Fab10 - Tower Semiconductor 300mm wafer fabrication facility at Agrate, Italy

Fab11 - Tower Semiconductor 300mm wafer fabrication facility at Rio Rancho, NM